L Number	Hits	Search Text	DB	Time stamp
1	6	semiconductor and (transducer with resonator) and (electrode\$1 with (al or aluminum or aluminium or Ti or titanium)) and (substrate with (silicon or si or GaAs or gallium)) and (piezoelectric with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/17 16:25
-	5884	("AlN.sub.3" or (aluminum adj nitride) or ZnO or (zinc adj oxide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/15
_	2657	(semiconductor and piezoelectric and electrode) and (thin with film)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/09
_	2	((semiconductor and piezoelectric and electrode) and (thin with film)) and (CMP and reflow and (lift with off))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/09
_	29	((semiconductor and piezoelectric and electrode) and (thin with film)) and (CMP or reflow or (lift with off)) and (stress with reduc\$4)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/09 16:02
-	0	(semiconductor and piezoelectric and electrode) and (burried with electrode)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/09 16:02
_	72	(semiconductor and piezoelectric and electrode) and (buried with electrode)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/09 16:02
_	5884	semiconductor and piezoelectric and electrode	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/10 10:01
-	206	(semiconductor and piezoelectric and electrode) and flush	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/11 11:45
_	206	(semiconductor and piezoelectric and electrode) and flush	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/11 13:23
-	2435	(semiconductor and piezoelectric and electrode) and (thin adj film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/11 13:41
-	75	((semiconductor and piezoelectric and electrode) and (thin adj film)) and planarization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/11 15:03
_	15	semiconductor and (thin with film with resonator) and CMP	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/11 15:45

_	103	semiconductor and (thin with film with resonator) and planar\$4	USPAT; US-PGPUB; EPO; JPO;	2003/09/11
			DERWENT; IBM TDB	
_	574	resonator and piezoelectric and electrode	USPAT;	2003/09/15
		and (planar or planarized or	US-PGPUB;	09:47
		planarization)	EPO; JPO; DERWENT;	
			IBM_TDB	
-	412	(resonator and piezoelectric and electrode and (planar or planarized or	USPAT; US-PGPUB;	2003/09/15
		planarization)) and thin	EPO; JPO;	03.47
			DERWENT;	
_	249	(resonator and piezoelectric and	IBM_TDB USPAT;	2003/09/15
		electrode and (planar or planarized or	US-PGPUB;	13:11
		planarization)) and (thin adj film)	EPO; JPO; DERWENT;	
			IBM_TDB	
-	1257	semiconductor and piezoelectric and (thin with film) and electrode and ((silicon	USPAT; US-PGPUB;	2003/09/15 13:15
		adj oxide) or "SiO.sub.2")	EPO; JPO;	13.13
			DERWENT;	
_	770	 (semiconductor and piezoelectric and	IBM_TDB USPAT;	2003/09/15
		(thin with film) and electrode and	US-PGPUB;	13:13
		((silicon adj oxide) or "SiO.sub.2")) and (planar\$4 or flat)	EPO; JPO; DERWENT;	
			IBM_TDB	
-	7	semiconductor and (piezoelectric with ((planar or flat) adj surface)) and (thin	USPAT; US-PGPUB;	2003/09/15
		with film) and electrode and ((silicon	EPO; JPO;	13.23
		adj oxide) or "SiO.sub.2")	DERWENT; IBM TDB	
_	12	semiconductor and (piezoelectric with	USPAT;	2003/09/15
		((planar or flat) adj surface)) and electrode and ((silicon adj oxide) or	US-PGPUB; EPO; JPO;	13:29
		"SiO.sub.2")	DERWENT;	
	5	/somiconduston and /mingonlastmic with	IBM_TDB USPAT;	2003/09/15
_	3	(semiconductor and (piezoelectric with ((planar or flat) adj surface)) and	US-PGPUB;	13:28
		electrode and ((silicon adj oxide) or	EPO; JPO;	
		"SiO.sub.2")) not (semiconductor and (piezoelectric with ((planar or flat) adj	DERWENT; IBM TDB	
		surface)) and (thin with film) and	_	
		electrode and ((silicon adj oxide) or "SiO.sub.2"))		
-	3	semiconductor and (((aluminum adj	USPAT;	2003/09/15
		nitride) or "AlN.sub.3" or (zinc adj oxide)) with ((planar or flat) adj	US-PGPUB; EPO; JPO;	13:34
		surface)) and electrode and ((silicon adj	DERWENT;	
_	537	oxide) or "SiO.sub.2") semiconductor and (piezo) and electrode	IBM_TDB USPAT;	2003/09/15
	337	and ((silicon adj oxide) or "SiO.sub.2")	US-PGPUB;	14:46
			EPO; JPO;	
			DERWENT; IBM TDB	
-	11	"781820"	USPĀT;	2003/09/15
			US-PGPUB; EPO; JPO;	14:57
			DERWENT;	
	2	("5410208").PN.	<pre>IBM_TDB USPAT;</pre>	2003/09/15
	-		US-PGPUB;	15:05
			EPO; JPO; DERWENT;	
			IBM TDB	
				··· · · · · · · · · · · · · · · · · ·

US-PGPUB; FPO, JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; U					
Prof. JPFC DERWENT: IBM TDB USPAT; US-PGPUB; EPFC, JPFC DERWENT: IBM TDB USPAT; US-PGPUB; EPFC JPFC DERWENT: IBM TDB	-	2	("5898348").PN.	USPAT;	2003/09/15
-					15:07
-					
- 4 (("6377135") or ("6351055")).PN. USPĀT; US-PCPUB; EPO; JPO; DERWENT; IRM TDB USPĀT; US-PCPUB; EPO; JPO; DE				DERWENT;	
15:10				_	
-	-	4	(("6377135") or ("6351055")).PN.	,	1
DERMENT; IRM TDB 2003/09/15 15:40 2003/09/15 15:40 2003/09/15 15:40 2003/09/15 15:40 2003/09/15 2003					15:10
-				1	
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15:40 15:40 15:40 15:40 15:40 15:40 15:40 15:40 15:40 15:40 15:40 15:40 15:40 15:40 15:41 15:45 15:4				_	
Semiconductor and (buried adj electrode) Semiconductor electrode Semiconductor Semicon	-	4	(("5608362") or ("5350965")).PN.	USPAT;	
DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB U					15:40
Semiconductor and (buried adj electrode)					
Semiconductor and (buried adj electrode)					
- 11 (semiconductor and (buried adj electrode)) and piezoelectric USPAT; 15:45	_	351	semiconductor and (buried adj electrode)		
- 11 (semiconductor and (buried adj electrode)) and piezoelectric					15:41
Semiconductor and (buried adj electrode) and piezoelectric SPAT; 2003/09/15 15:45 EPO; JPO; DERWENT; IBM_TDB USPAT; 2003/09/15 15:49 EPO; JPO; DERWENT; IBM_TDB USPAT; 2003/09/15 EPO; JPO; DERWENT; IBM_TDB USPAT; USPEQUB; EPO; JPO; DERWENT; IBM_TDB USPAT; EPO; JPO;				EPO; JPO;	
1					
electrode) and piezoelectric US-PGPUB; EPO; JPO; DERWENN; IBM TDB USPAT; 2003/09/15 15:49 15:49 15:49 15:49 15:49 15:49 15:49 15:49 15:49 15:49 15:49 15:49 15:49 16:49					
Committee Comm	_	11		USPAT;	
Commitment Com			electrode)) and piezoelectric	US-PGPUB;	15:45
- 27 (semiconductor and (buried adj electrode)) and planarization - 1 ((semiconductor and (buried adj electrode)) and planarization) - 1 ((semiconductor and (buried adj electrode)) and planarization) and (plezoelectric or "Aln.sub.3" or "ZnO") - 1451 semiconductor and transducer\$1 and electrode and planar\$4 - 1451 semiconductor and transducer\$1 and electrode and planar\$4 - 634 (semiconductor and transducer\$1 and electrode and planar\$4) and plezoelectric - 527 ((semiconductor and transducer\$1 and electrode and planar\$4) and plezoelectric - 13 (((semiconductor and transducer\$1 and electrode and planar\$4) and plezoelectric plexwent; IBM_TDB uspAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB uspAT; US-PGPUB; EPO; JPO; DE				EPO; JPO;	
27					
electrode)) and planarization Commission				IBM_TDB	
Committee Comm	_	27			2003/09/15
Commitment of the property o					15:49
Commitment of the property o			-	EPO; JPO;	
Commitment of the property o				DERWENT;	
electrode)) and planarization) and (piezoelectric or "AlN.sub.3" or "ZnO") EPGPUB; EPG; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB				IBM_TDB	
(piezoelectric or "AlN.sub.3" or "Zno") [PO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TD	_	1	((semiconductor and (buried adj	USPAT;	2003/09/15
(piezoelectric or "AlN.sub.3" or "ZnO") [PO; JPO; DERWENT; IBM_TDB uspAT; Us-PGPUB; EPO; JPO; DERWENT; IBM_TDB uspAT; U			electrode)) and planarization) and	US-PGPUB;	15:50
DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; IBM_TDB US-PGPUB;			(piezoelectric or "AlN.sub.3" or "ZnO")		
- 1451 semiconductor and transducer\$1 and electrode and planar\$4				DERWENT;	
electrode and planar\$4 Semiconductor and transducer\$1 and electrode and planar\$4 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; or "SiO.sub.2") Siousion of transducer\$1 and electrode and planar\$4 and piezoelectric and ((silicon ajd oxide) or "Siousub.2") Siousion of transducer\$1 and electrode and planar\$4 and piezoelectric and ((silicon ajd oxide) or "Siousub.2") and cmp Siousion of transducer\$1 and USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; D				IBM_TDB	
- 634 (semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWEN	_	1451			1
- 634 (semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; or "SiO.sub.2") - 13 (((semiconductor and transducer\$1 and electrode and planar\$4) and electrode and planar\$4) and electrode and planar\$4) and electrode and planar\$4) and EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; I			electrode and planar\$4	US-PGPUB;	16:18
- 634 (semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; Electrode and planar\$4) and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2") - 13 (((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2") - 13 (((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2")) and cmp - 2 (((semiconductor and transducer\$1 and USPAT; 2003/09/15)				EPO; JPO;	
- 634 (semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 527 ((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2") - 13 (((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2") - 2 (((semiconductor and transducer\$1 and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2")) and cmp - 2 (((semiconductor and transducer\$1 and US-PGPUB; DERWENT; IBM_TDB US-PGPUB; IBM_T				DERWENT;	
electrode and planar\$4) and piezoelectric US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; 2003/09/15 electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2") 13 (((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2")) and cmp 2 (((semiconductor and transducer\$1 and USPAT; IBM_TDB USPAT;				IBM_TDB	
- 527 ((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2") - 13 (((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2") - 2 (((semiconductor and transducer\$1 and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2")) and cmp - 2 (((semiconductor and transducer\$1 and USPAT; IBM_TDB USPAT	_	634		USPAT;	2003/09/15
- 527 ((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2") - 13 (((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2")) - 2 (((semiconductor and transducer\$1 and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2")) and cmp - 2 (((semiconductor and transducer\$1 and USPAT; IBM_TDB USPA			electrode and planar\$4) and piezoelectric	US-PGPUB;	16:19
- 527 ((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2") - 13 (((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2")) and cmp - 2 (((semiconductor and transducer\$1 and piezoelectric) and cmp - 2 (((semiconductor and transducer\$1 and USPAT; IBM_TDB USPAT; I					
- S27 ((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2") - 13 (((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2")) and cmp - 2 (((semiconductor and transducer\$1 and piezoelectric) and cmp - 2 (((semiconductor and transducer\$1 and USPAT; IBM_TDB USPAT; I				DERWENT;	
electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2") DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; END_TDB					
electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2") DERWENT; IBM_TDB (((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2")) and cmp Comparison of the piezoelectric or "SiO.sub.2")) and cmp Comparison of transducer\$1 and comp DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; DERWENT; IBM_TDB USPAT; 2003/09/15	-	527			,
or "SiO.sub.2") DERWENT; IBM_TDB USPAT; electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2")) and cmp DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; 2003/09/15			electrode and planar\$4) and		16:19
- 13 (((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2")) and cmp - 2 (((semiconductor and transducer\$1 and USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; 2003/09/15					
- 13 (((semiconductor and transducer\$1 and electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) or "SiO.sub.2")) and cmp 2 (((semiconductor and transducer\$1 and USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; 2003/09/15			or "SiO.sub.2")	L .	
electrode and planar\$4) and piezoelectric) and ((silicon ajd oxide) priezoelectric) and cmp DERWENT; IBM_TDB USPAT; 2003/09/15					
piezoelectric) and ((silicon ajd oxide) cor "SiO.sub.2")) and cmp DERWENT; IBM_TDB 2 (((semiconductor and transducer\$1 and USPAT; 2003/09/15	_	13			
or "SiO.sub.2")) and cmp DERWENT; IBM_TDB (((semiconductor and transducer\$1 and USPAT; 2003/09/15					16:22
- 2 (((semiconductor and transducer\$1 and USPAT; 2003/09/15				· ·	
- 2 (((semiconductor and transducer\$1 and USPAT; 2003/09/15			or "SiO.sub.2")) and cmp	DERWENT;	
electrode and planar\$4) and US-PGPUB: 16:29	_	2	(((semiconductor and transducer\$1 and	USPAT;	2003/09/15
			electrode and planar\$4) and	US-PGPUB;	16:29
piezoelectric) and ((silicon ajd oxide) EPO; JPO;				EPO; JPO;	
or "SiO.sub.2")) and (piezoelectric with DERWENT;					
defects) IBM_TDB			· · · · · · · · · · · · · · · · · · ·		
- 83 (381/353).CCLS. USPAT; 2003/09/15	_	83	(381/353).CCLS.	1	
US-PGPUB; 16:31					16:31
EPO; JPO;					
DERWENT;				1	
IBM_TDB					
- 186 (piezoelectric with film) and (patterned USPAT; 2003/09/16	-	186		USPAT;	· · · · · · · · · · · · · · · · · · ·
with electrode) and dielectric US-PGPUB; 10:17			with electrode) and dielectric		10:17
EPO; JPO;					
DERWENT;		ı		L DERWENT:	1
IBM TDB				l .	

_	20	("3582691" "4054808" "4240002" "4363991" "4461179" "4578611" "4611141" "4651310" "4680595" "4732351" "4761582" "4849668" "4857887" "4864179" "4914565" "5305507" "5315203" "5415175" "5438998" "5493541").PN.	USPAT	2003/09/16 10:12
_	16	5456996 5495541 PN. 5656882.URPN.	USPAT	2003/09/16
_	25	("3582691" "4054808" "4240002" "4363991" "4458173" "4461179" "4578611" "4611141" "4651310" "4680595" "4732351" "4742264" "4761582" "4849668" "4857887" "4864179" "4914565" "5305507" "5315203" "5404067" "5415175" "5438998" "5493541" "5632841" "5656882").PN.	USPAT	2003/09/16 10:15
-	3	6069433.URPN.	USPAT	2003/09/16 10:16
_	359	(piezoelectric) and (thin adj film) and (patterned with electrode) and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 10:17
-	186	(piezoelectric with film) and (patterned with electrode) and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 12:00
-	194	((piezoelectric) and (thin adj film) and (patterned with electrode) and dielectric) not ((piezoelectric with film) and (patterned with electrode) and dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16
-	20	((aluminum adj nitride) or "AlN.sub.3" or (zinc adj oxide) or "ZnO") same (thin adj film) and ((patterned adj electrode\$1) same dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 11:43
_	1	((aluminium adj nitride) or "AlN.sub.3" or (zinc adj oxide) or "ZnO") same (thin adj film) and ((patterned adj electrode\$1) same dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 11:43
_	2346		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16
_	36	barber.in. and piezoelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16
_	3	piezoelectric same (weakening adj effect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 11:51
_	222	piezoelectric same (internal adj stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/09/16 12:00
_	4	(piezoelectric same (internal adj stress)) and (patterned adj electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 11:55

-	0	piezoelectric and ((patterned adj	USPAT;	2003/09/16
		electrode\$1) same (dielectric adj	US-PGPUB;	11:55
		sidewalls))	EPO; JPO; DERWENT;	
			IBM TDB	
_	0	piezoelectric and ((patterned adj	USPAT;	2003/09/16
		electrode\$1) same (dielectric with side))	US-PGPUB;	11:56
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	0	piezoelectric and ((patterned adj	USPAT;	2003/09/16
		electrode\$1) same (dielectric with	US-PGPUB; EPO; JPO;	11:56
1		spacers))	DERWENT;	
			IBM TDB	
_	25	piezoelectric and ((patterned adj	USPAT;	2003/09/16
		electrode\$1) same (dielectric with	US-PGPUB;	11:57
		layer))	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	1790	piezoelectric with membrane	USPAT;	2003/09/16
			US-PGPUB;	11:58
			EPO; JPO; DERWENT;	
			IBM TDB	
_	31	(piezoelectric with membrane) and	USPAT;	2003/09/16
	-	(patterned adj electrode\$1)	US-PGPUB;	12:01
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	805	(piezoelectric with membrane) and	USPAT;	2003/09/16
		(electrode\$1)	US-PGPUB; EPO; JPO;	11:59
			DERWENT;	
			IBM TDB	
_	774	((piezoelectric with membrane) and	USPAT;	2003/09/16
1		(electrode\$1)) not ((piezoelectric with	US-PGPUB;	12:00
		membrane) and (patterned adj	EPO; JPO;	
		electrode\$1))	DERWENT;	
<u> </u>	774	///niogoologtrig with mambanal and	IBM_TDB	2003/09/16
-	774	<pre>(((piezoelectric with membrane) and (electrode\$1)) not ((piezoelectric with</pre>	USPAT; US-PGPUB;	2003/09/16
		membrane) and (patterned adj	EPO; JPO;	12.00
		electrode\$1))) not (piezoelectric and	DERWENT;	
		((patterned adj electrode\$1) same	IBM_TDB	
		(dielectric with layer)))	_	
-	774	((((piezoelectric with membrane) and	USPAT;	2003/09/16
		(electrode\$1)) not ((piezoelectric with	US-PGPUB;	12:00
		membrane) and (patterned adj	EPO; JPO;	
		electrode\$1))) not (piezoelectric and ((patterned adj electrode\$1) same	DERWENT; IBM TDB	
		(dielectric with layer)))) not		
		(("3582691" "4054808" "4240002"		
		"4363991" "4461179" "4578611"		
		"4611141" "4651310" "4680595"		
		"4732351" "4761582" "4849668"		
		"4857887" "4864179" "4914565" "5305507" "5315303" "5415175"		
		"5305507" "5315203" "5415175" "5438998" "5493541").PN.)		
		"5438998" "5493541").PN.)	L	J

			T	0000/00/55
-	772	(((((piezoelectric with membrane) and (electrode\$1)) not ((piezoelectric with	USPAT; US-PGPUB;	2003/09/16
]		membrane) and (patterned adj	EPO; JPO;	12.00
		electrode\$1))) not (piezoelectric and	DERWENT;	
		((patterned adj electrode\$1) same	IBM TDB	
		(dielectric with layer)))) not	_	
		(("3582691" "4054808" "4240002"	1	
		"4363991" "4461179" "4578611"		
		"4611141" "4651310" "4680595"		
		"4732351" "4761582" "4849668"		
		"4857887" "4864179" "4914565"		
		"5305507" "5315203" "5415175" "5438998" "5493541").PN.)) not		
		(((piezoelectric) and (thin adj film) and		
		(patterned with electrode) and		
		dielectric) not ((piezoelectric with		
		film) and (patterned with electrode) and		
		dielectric))		
_	750	(((((piezoelectric with membrane) and	USPAT;	2003/09/16
1		(electrode\$1)) not ((piezoelectric with	US-PGPUB;	12:01
		membrane) and (patterned adj	EPO; JPO;	
		electrode\$1))) not (piezoelectric and	DERWENT;	
		((patterned adj electrode\$1) same	IBM_TDB	
		(dielectric with layer)))) not		
		(("3582691" "4054808" "4240002"		
		"4363991" "4461179" "4578611" "4611141" "4651310" "4680595"		
		"4611141" "4651310" "4680595" "4732351" "4761582" "4849668"		
		"4857887" "4864179" "4914565"		
		"5305507" "5315203" "5415175"		
		"5438998" "5493541").PN.)) not		
		(((piezoelectric) and (thin adj film) and		
		(patterned with electrode) and ,		
		dielectric) not ((piezoelectric with		
]		film) and (patterned with electrode) and		
[dielectric))) not ((piezoelectric with		
		<pre>film) and (patterned with electrode) and dielectric)</pre>		
_	179	<pre>(((((((piezoelectric with membrane) and</pre>	USPAT;	2003/09/16
	1,5	(electrode\$1)) not ((piezoelectric with	US-PGPUB;	12:01
		membrane) and (patterned adj	EPO; JPO;	
		electrode\$1))) not (piezoelectric and	DERWENT;	
		((patterned adj electrode\$1) same	IBM_TDB	
		(dielectric with layer)))) not		
		(("3582691" "4054808" "4240002"		
		"4363991" "4461179" "4578611"		
		"4611141" "4651310" "4680595" "4732351" "4761592" "4849669"		
		"4732351" "4761582" "4849668" "4857887" "4864179" "4914565"		
		"5305507" "5315203" "5415175"		
		"5438998" "5493541").PN.)) not		
		(((piezoelectric) and (thin adj film) and		
		(patterned with electrode) and		
		dielectric) not ((piezoelectric with		
		film) and (patterned with electrode) and		
		dielectric))) not ((piezoelectric with		
		film) and (patterned with electrode) and		
_	210	dielectric)) and semiconductor	IICDATI.	2002/00/17
_	218	semiconductor and (lower with thickness with electrode\$1) and piezoelectric	USPAT; US-PGPUB;	2003/09/17
		with electionedil and bissostectife	EPO; JPO;	10.20
			DERWENT;	
			IBM TDB	
-	18	semiconductor and ((reduce or reduced or	USPAT;	2003/09/17
		reducing or thinning or thinned) with	US-PGPUB;	10:21
		lower with thickness with electrode\$1)	EPO; JPO;	
		and piezoelectric	DERWENT;	
			IBM TDB	

-	133	capacitor same barrier same perovskite	USPAT;	2003/09/17
			US-PGPUB;	13:53
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	("6545392").PN.	USPĀT;	2003/09/17
	~	(0010032	US-PGPUB;	13:55
			EPO; JPO;	120.00
			DERWENT;	
			IBM TDB	
_	2	("6307305").PN.	USPAT;	2003/09/17
		(0507505).111.	US-PGPUB;	13:55
			EPO; JPO;	1 13.33
			DERWENT;	
			IBM TDB	
· _	2	("6225877").PN.	USPAT;	2003/09/17
		(0223077).PN.	US-PGPUB;	13:57
			EPO; JPO;	13.37
			DERWENT;	
			IBM TDB	
	274	piezoelectric adj membrane	USPAT;	2003/09/17
_	2/4	prezoerectric adj membrane	US-PGPUB;	13:58
			EPO; JPO;	13:56
			DERWENT;	
	142	(mingaalagtuig adi mambuana) and	IBM_TDB	2002/00/17
-	142	, 'E	USPAT;	2003/09/17
		electrode\$1	US-PGPUB;	13:58
			EPO; JPO;	
} i			DERWENT;	
			IBM_TDB	2002/00/17
-	29	((piezoelectric adj membrane) and	USPAT;	2003/09/17
		electrode\$1) and ((si or silicon or	US-PGPUB;	13:59
		gallium or GAAS) with substrate)	EPO; JPO;	
[DERWENT;	
			IBM TDB	1